



SHEET 1 OF 1

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.
60188-585SERIAL NO.
10/620,614APPLICANT
Kunisato YAMAOKA, et al.FILING DATE
July 17, 2003GROUP
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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US			
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FOREIGN PATENT DOCUMENTS

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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
HWS		Yeonbae chung et al., "A 3.3-V 4-Mb Nonvolatile Ferroelectric RAM with Selectively-Driven Double-Pulsed Plate Read/Write-Back Scheme," Symposium on VLSI Circuits Digest of Technical Papers, pp. 97-97, 1999.

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